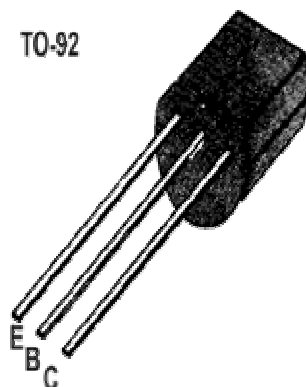


APPLICATION: General Purpose Amplifier Application.

—PNP silicon—

MAXIMUM RATING (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V _{CB0}	-60	V
Collector-emitter voltage	V _{CEO}	-60	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current	I _C	-600	mA
Collector Power Dissipation	P _C	600	mW
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	- 55~150	°C



ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
Common Emitter DC Current Gain	h _{FE}	100		300		V _{CE} = -10V, I _C = -150mA
Collector Cut-off Current	I _{CBO}			-0.1	μA	V _{CB} =-50 V, I _E =0
Emitter Cut-off Current	I _{EBO}			-0.1	μA	V _{EB} =-3 V, I _C =0
Collector-Base Breakdown Voltage	BV _{CB0}	-60			V	I _C = -0.1mA, I _E =0
Collector-Emitter Breakdown Voltage	BV _{CEO}	-60			V	I _C =- 1 mA, I _B =0
Emitter-Base Breakdown Voltage	BV _{EBO}	-5			V	I _E = -0.1mA, I _C =0
Collector-Emitter Saturation Voltage	V _{CE(sat)}			-0.5	V	I _C =- 500 mA, I _B = -50 mA
Base-Emitter Saturation Voltage	V _{BE(sat)}			-1.3	V	I _C =- 500 mA, I _B = -50 mA
Gain bandwidth product	f _T	200			MHz	I _C = -50 mA, V _{CE} =- 20 V, f = 100 MHz
Common Base Output Capacitance	C _{ob}			8	PF	V _{CB} =- 10 V, I _E =0, f = 1 MHz
Turn on Time	t _{on}			45	ns	V _{CC} =- 30 V, I _C = -150 mA, I _{B1} =-15mA
Turn off Time	t _{off}			100	ns	V _{CC} =-6 V, I _C =- 150 mA, I _{B1} =I _{B2} =-15mA

h_{FE} Classification

Classification

h_{FE} 100~300